ABSTRACT

METHOD OF FABRICATING A TWIN HAMMER TREE SHAPED CAPACITOR STRUCTURE FOR A DRAM DEVICE

A process for fabricating a large surface area, storage node structure, for a DRAM device, has been developed. The storage node structure is comprised of a lower level polysilicon structure, exhibiting a "twin hammer tree" shape, and connected to an upper polysilicon level, exhibiting a "branch" type shape. The fabrication process used to create this storage node structure, features various deposition procedures, used for insulator and polysilicon layers, and various anisotropic and isotropic, dry etch procedures, as well as wet etch procedures, used for creation of the "twin hammer tree" shaped structure.

(FIGURE 1 IS SUGGESTED FOR PUBLICATION)